Patent
VT0291-US1

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IB 621 467 10X US
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May 4, 2001
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Steven M. Mitchell
(Typed or printed name of person mailing application)

(Signature of person mailing application)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hemphill, et al.
Serial No: to be assigned
Filed: herewith
For: "Non-Uniform Etching Of Anode Foil To Produce Higher Capacitance Gain Without Sacrificing Foil Strength"

: Date: May 4, 2001
: Group Art Unit: not known
: Examiner: not yet known

PRELIMINARY AMENDMENT

Honorable Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the above-captioned patent application as follows:

In the specification:

On page 3, please replace paragraph 7 with the following rewritten paragraph:

The ideal etching structure is a pure tunnel-like etch with defined and uniform tunnel diameters and without any undesirable pitting of the foil. As tunnel density (*i.e.*, the number of tunnels per square centimeter) is increased, a corresponding enlargement of the overall surface area will occur. Larger surface area results in higher overall capacitance. However, as tunnel density increases, more of the aluminum foil is removed, reducing the strength of the remaining foil. Therefore a compromise must be made between foil strength and capacitance gain.

Attached hereto is a marked-up version of the changes made to the specification by the preliminary amendment. The attachment is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE".

Please charge any fees or credit overpayment to Deposit Account No. 22-0265. If any addition extension fee is required, please charge to Deposit Account No. 22-0265. This form is submitted in triplicate.

Respectfully submitted,

Steven M. Mitchell
Reg. No. 31,857
Attorney for Applicant

PACESETTER, INC.
701 E. Evelyn Avenue
Sunnyvale, CA 94086
Telephone: (408) 522-6101
Date: May 4, 2001

VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the specification:

On page 3, paragraph 7 has been amended as follows:

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